

ABSTRACT OF THE DISCLOSURE

It is an object of the present invention to adjust the transfer environment of a substrate in order to prevent contamination of the substrate surface by impurities. A semiconductor manufacturing apparatus comprises a load-lock chamber 1 in which substrate exchange with the outside is performed, a wafer process chamber 2 in which the wafer is subjected to a predetermined processing, and a transfer chamber 3 in which the wafer is transferred between the load-lock chamber 1 and the wafer process chamber 2. In a semiconductor manufacturing method in which this semiconductor manufacturing apparatus is used to treat a substrate, an inert gas ( $N_2$ ) is supplied to and exhausted from the load-lock chamber 1, the transfer chamber 3, and the wafer process chamber 2 while the substrate is being transferred from the load-lock chamber 1 to the wafer process chamber 2 through the transfer chamber 3, and the substrate transfer is carried out with a predetermined pressure maintained.